

### General Description

The WSD30L55DN33 is the highest performance trench Dual P-Channel MOSFET with extreme high cell density, which provide excellent  $R_{DS(ON)}$  and gate charge for most of the synchronous buck converter applications.

The WSD30L55DN33 meet the RoHS and Green Product requirement, 100%  $E_{AS}$  guaranteed with full function reliability approved.

### Features

- 100% UIS +  $R_g$  Tested.
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

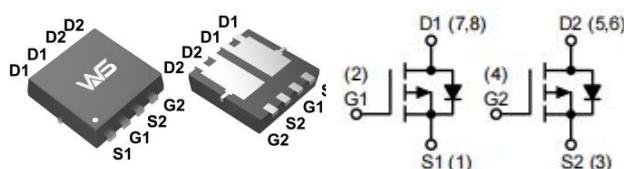
### Product Summary

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$
-30V	15mΩ	-15A

### Applications

- Power Management for Industrial DC/DC Converters
- Motor Control

### DFN3x3-8L Pin Configuration



### Absolute Maximum Ratings ( $T_A=25^{\circ}\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter		Rating	Units
$V_{DS}$	Drain-Source Voltage		-30	V
$V_{GS}$	Gate-Source Voltage		$\pm 20$	
$I_D$ <sup>7</sup>	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	-15	A
		$T_C=100^{\circ}\text{C}$	-11	
$I_{DM}$ <sup>3</sup>	Pulse Drain Current		-45	W
$P_D$ <sup>2</sup>	Power Dissipation	$T_C=25^{\circ}\text{C}$	42	
		$T_C=100^{\circ}\text{C}$	17	
$I_{AS}$ <sup>3</sup>	Single pulse Avalanche Current		-15	A
$E_{AS}$ <sup>3</sup>	Single pulse Avalanche Energy	$L=0.3\text{mH}$	12	mJ
$T_{STG}$	Storage Temperature Range		-55 to 150	$^{\circ}\text{C}$
$T_J$	Operating Junction Temperature Range		-55 to 150	
$R_{\theta JA}$ <sup>1,4</sup>	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	43	$^{\circ}\text{C/W}$
		Steady State	80	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		3	

**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , Unless Otherwise Noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=-250\mu A$	-30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V$ , $I_D=-5A$	---	15	18	m $\Omega$
		$T_J=125^{\circ}\text{C}$	---	19	---	
		$V_{GS}=-4.5V$ , $I_D=-2A$	---	18	21	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=-250\mu A$	-1.2	-1.6	-2.0	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-24V$ , $V_{GS}=0V$	---	---	-1.0	$\mu A$
		$T_J=55^{\circ}\text{C}$	---	---	-30	
$I_{GSS}$	Gate-Source Leakage Current	$V_{DS}=0V$ , $V_{GS}=\pm 20V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=-5V$ , $I_D=-2.5A$	---	8	---	S
$R_G$	Gate Resistance	$f=1.0\text{MHz}$	---	2.8	---	$\Omega$
$Q_g$	Total Gate Charge (10V)	$V_{DS}=-15V$ , $V_{GS}=-4.5V$ , $I_D=-4A$	---	14.3	21	nC
$Q_g$	Total Gate Charge (4.5V)		---	7	11	
$Q_{gs}$	Gate-Source Charge		---	2	---	
$Q_{gd}$	Gate-Drain Charge		---	2.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=-15V$ , $V_{GS}=-10V$ , $I_D=-1A$ $R_L=1\Omega$ , $R_{GEN}=6\Omega$	---	11	---	ns
$T_r$	Rise Time		---	7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	29	---	
$T_f$	Fall Time		---	6	---	
$C_{iss}$	Input Capacitance	$V_{DS}=-15V$ , $V_{GS}=0V$ , $f=1.0\text{MHz}$	---	823	---	pF
$C_{oss}$	Output Capacitance		---	106	---	
$C_{rss}$	Reverse Transfer Capacitance		---	74	---	

**Diode Characteristics**

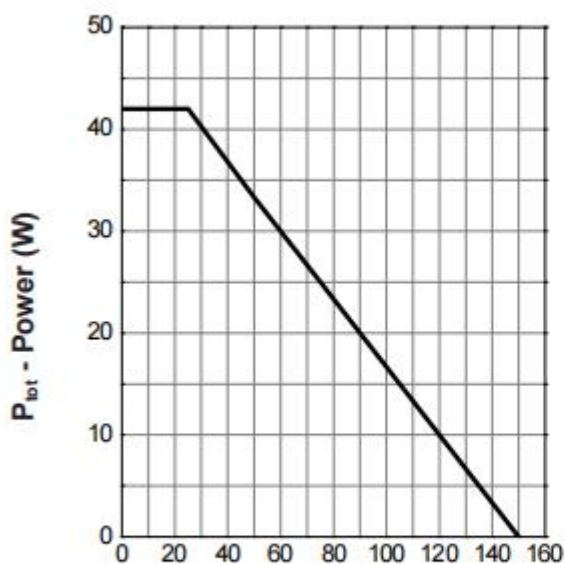
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$I_S^7$	Continuous Source Current		---	---	-15	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V$ , $I_S=-1A$	---	-0.7	-1.0	V
$t_{rr}$	Reverse Recovery Time	$I_F=-4A$ , $di/dt=500A/\mu s$	---	11	---	ns
$Q_{rr}$	Reverse Recovery Charge		---	2	---	nC

Note:

1. The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The Power dissipation  $P_{DSM}$  is based on  $R_{\theta JA} \leq 10s$  and the maximum allowed junction temperature of  $150^{\circ}\text{C}$ . The value in any given application depends on the user's specific board design.
2. The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^{\circ}\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
3. Single pulse width limited by junction temperature  $T_{J(MAX)}=150^{\circ}\text{C}$ .
4. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to case  $R_{\theta JC}$  and case to ambient.
5. The static characteristics in Figures 1 to 6 are obtained using  $<300\mu s$  pulses, duty cycle 0.5% max.
6. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of  $T_{J(MAX)}=150^{\circ}\text{C}$ . The SOA curve provides a single pulse rating.
7. The maximum current rating is package limited.
8. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ .
9. The maximum current rating is silicon limited

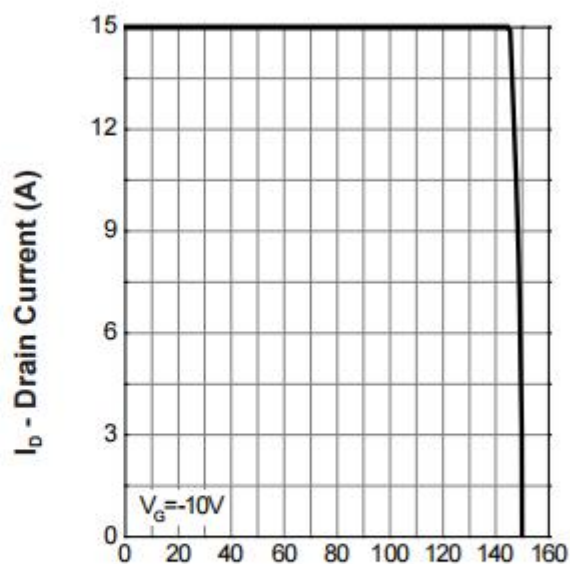
## Typical Characteristics

**Power Dissipation**



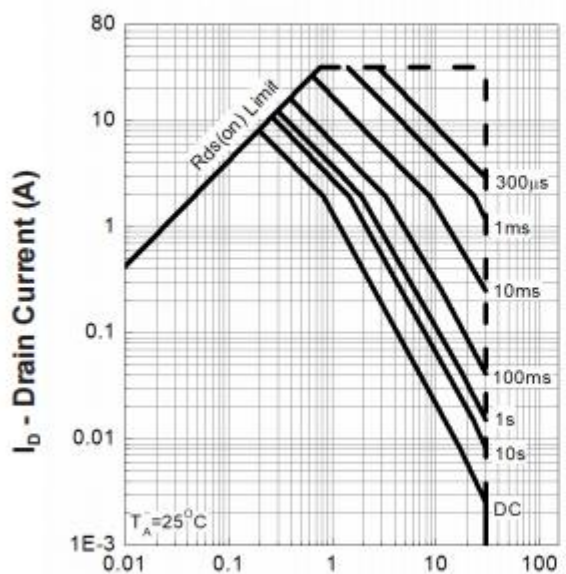
$T_c$  - Case Temperature ( $^{\circ}\text{C}$ )

**Drain Current**



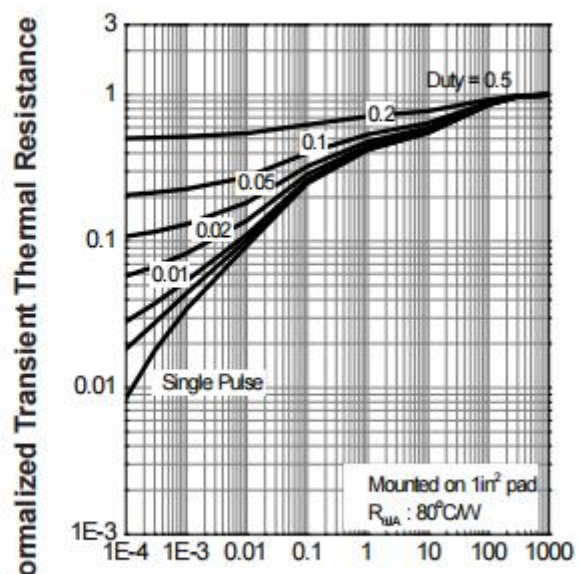
$T_c$  - Case Temperature ( $^{\circ}\text{C}$ )

**Safe Operation Area**



$-V_{DS}$  - Drain-Source Voltage (V)

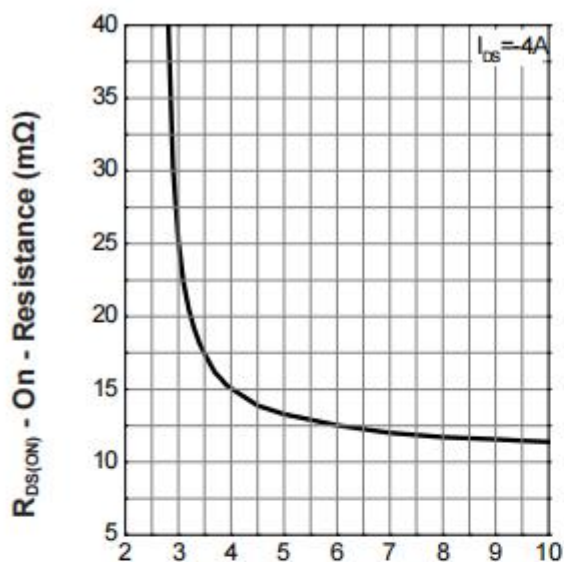
**Thermal Transient Impedance**



Square Wave Pulse Duration (sec)

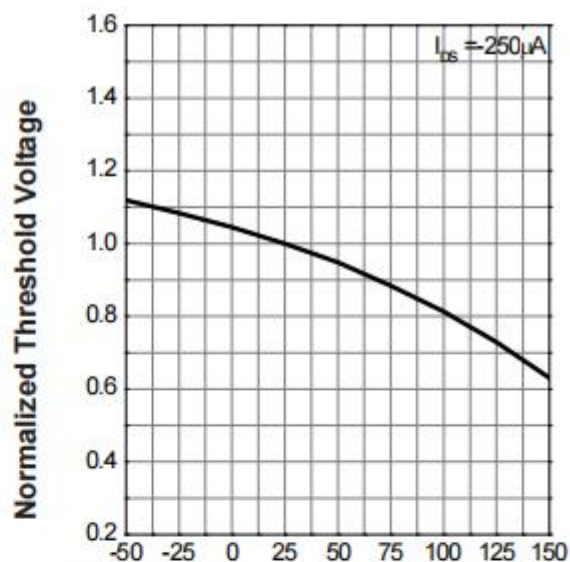
Typical Characteristics (Cont.)

Gate-Source On Resistance



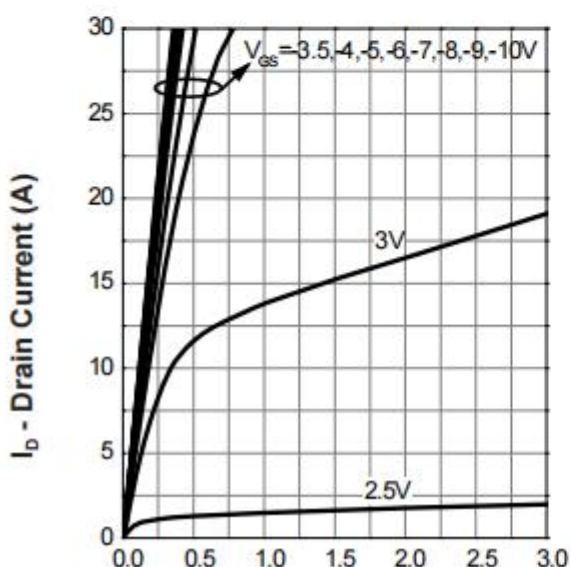
$-V_{GS}$  - Gate - Source Voltage (V)

Gate Threshold Voltage



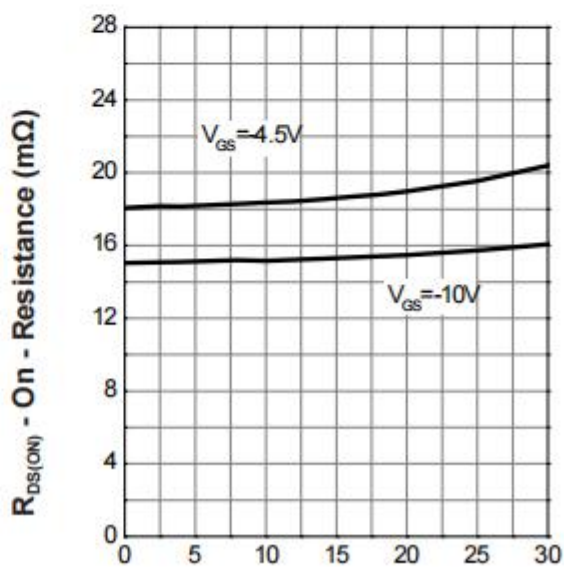
$-T_j$  - Junction Temperature (°C)

Output Characteristics



$-V_{DS}$  - Drain - Source Voltage (V)

Drain-Source On Resistance

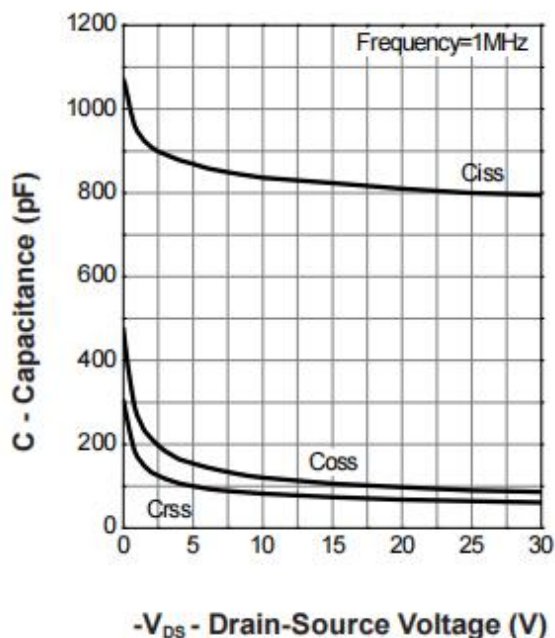


$-I_D$  - Drain Current (A)

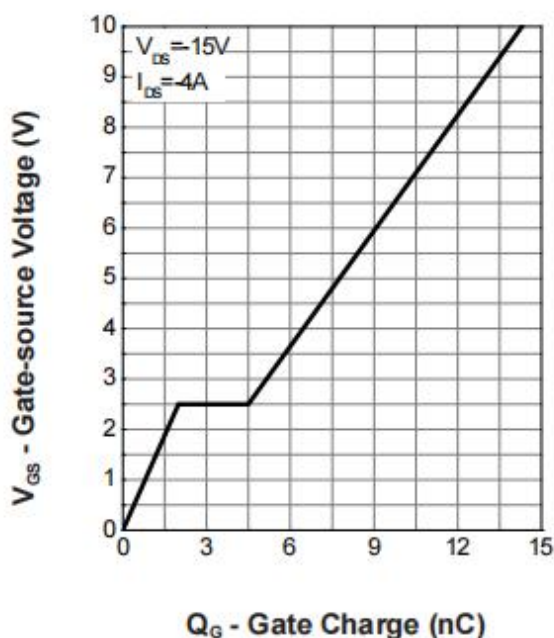


Typical Characteristics (Cont.)

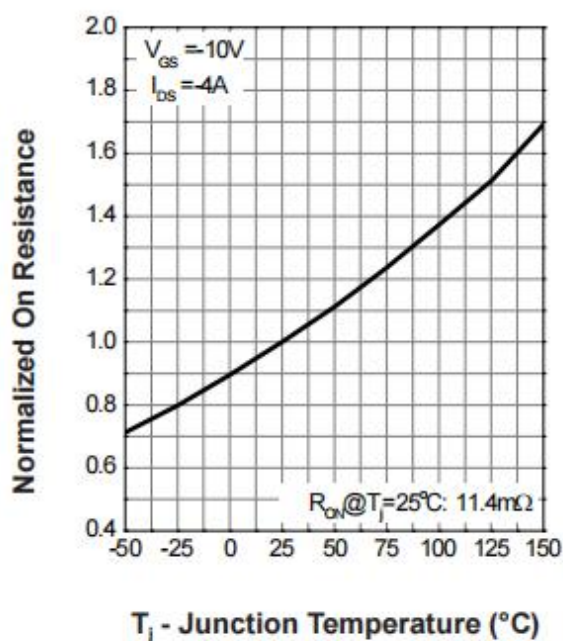
Capacitance



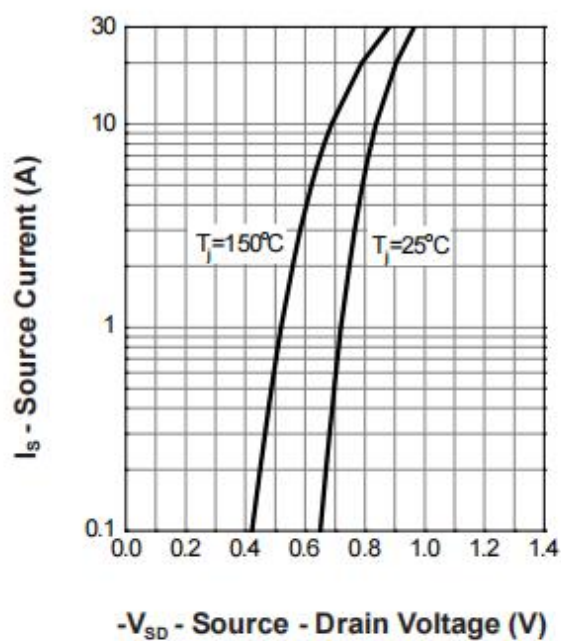
Gate Charge



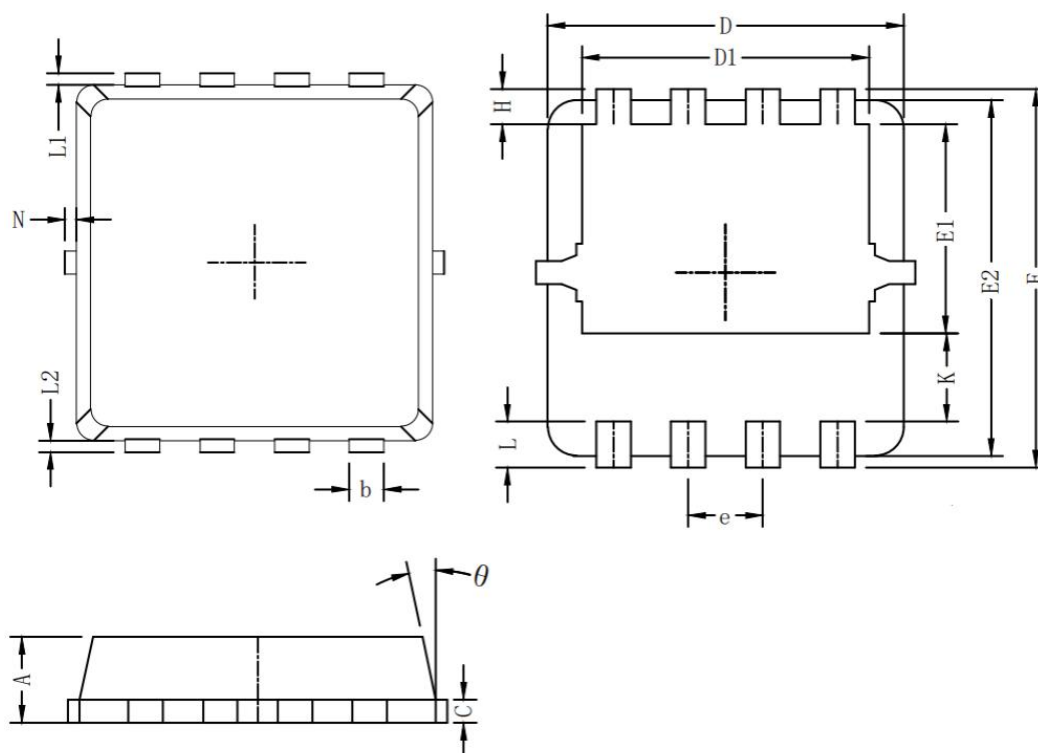
Drain-Source On Resistance



Source-Drain Diode Forward



# Packaging information



Symbol	Dim in mm		
	min	typ	max
A	0.6	0.75	0.9
b	0.2	0.3	0.4
C	0.15	0.2	0.25
D	3	3.1	3.2
D1	2.3	2.45	2.6
E	3.15	3.3	3.45
E1	1.43	1.73	1.93
E2	2.9	3.05	3.2
e	0.65BSC		
H	0.2	0.35	0.5
K	0.57	0.77	0.87
L	0.3	0.4	0.5
L1/L2	0.1REF		
$\theta$	8°	10°	13°
N	0		0.15

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